

Technical Digest for International conference

Opto-Electronic Integrated circuit

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InP MOVPE growth

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InP DFB lasers, InP strained MQW lasers

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InP Self-limiting Etching

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InP Molecular Layer Epitaxy

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GaN Blue Laser Diodes and Ultraviolet Light-Emitting Diodes

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GaN Power devices, GaN MMICs

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